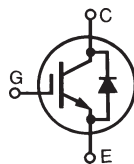


GenX3™ 1200V IGBT w/ Diode

MMIX1G120N120A3V1

(Electrically Isolated Tab)

Ultra-Low-Vsat PT IGBT for
3kHz Switching

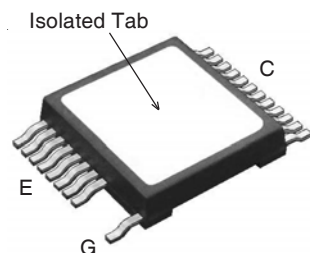
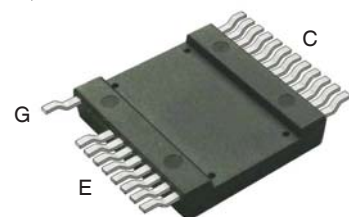


$$V_{CES} = 1200V$$

$$I_{C110} = 105A$$

$$V_{CE(sat)} \leq 2.2V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^{\circ}C$ to $150^{\circ}C$	1200	V
V_{CGR}	$T_J = 25^{\circ}C$ to $150^{\circ}C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^{\circ}C$	220	A
I_{C110}	$T_C = 110^{\circ}C$	105	A
I_{CM}	$T_C = 25^{\circ}C$, 1ms	700	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^{\circ}C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 240$ @ $0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^{\circ}C$	400	W
T_J		-55 ... +150	$^{\circ}C$
T_{JM}		150	$^{\circ}C$
T_{stg}		-55 ... +150	$^{\circ}C$
T_L	Maximum Lead Temperature for Soldering	300	$^{\circ}C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^{\circ}C$
V_{ISOL}	50/60Hz, 1 minute	2500	V~
F_C	Mounting Force	50..200/11..45	N/lb.
Weight		8	g



G = Gate
C = Collector

E = Emitter

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Optimized for Low Conduction losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^{\circ}C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ Note 2, $T_J = 125^{\circ}C$			50 μA 5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $T_J = 125^{\circ}C$	1.85 1.95		2.20 V V

Symbol Test Conditions(T_J = 25°C Unless Otherwise Specified)**Characteristic Values****Min. Typ. Max.**

g_{fs}	I _C = 60A, V _{CE} = 10V, Note 1	45	73	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		9900	pF
C_{oes}			655	pF
C_{res}			240	pF
Q_g	I _C = 120A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		420	nC
Q_{ge}			70	nC
Q_{gc}			180	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = 100A, V _{GE} = 15V V _{CE} = 960V, R _G = 1Ω Note 3		40	ns
t_{ri}			67	ns
E_{on}			10	mJ
t_{d(off)}			490	ns
t_{fi}			325	ns
E_{off}			33	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = 100A, V _{GE} = 15V V _{CE} = 960V, R _G = 1Ω Note 3		30	ns
t_{ri}			75	ns
E_{on}			15	mJ
t_{d(off)}			685	ns
t_{fi}			680	ns
E_{off}			58	mJ
R_{thJC}			0.31	°C/W
R_{thCS}		0.05		°C/W
R_{thJA}		30		°C/W

Reverse Diode (FRED)**Symbol Test Conditions**(T_J = 25°C Unless Otherwise Specified)**Characteristic Values****Min. Typ. Max.**

V_F	I _F = 100A, V _{GE} = 0V, Note 1		1.8	V
I_{RM}	I _F = 50A, V _{GE} = 0V, -di _F /dt = 200A/μs, V _R = 300V		20	A
t_{rr}			700	ns
R_{thJC}			0.50	°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Part must be heatsunk for high-temp I_{ces} measurement.
3. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G.

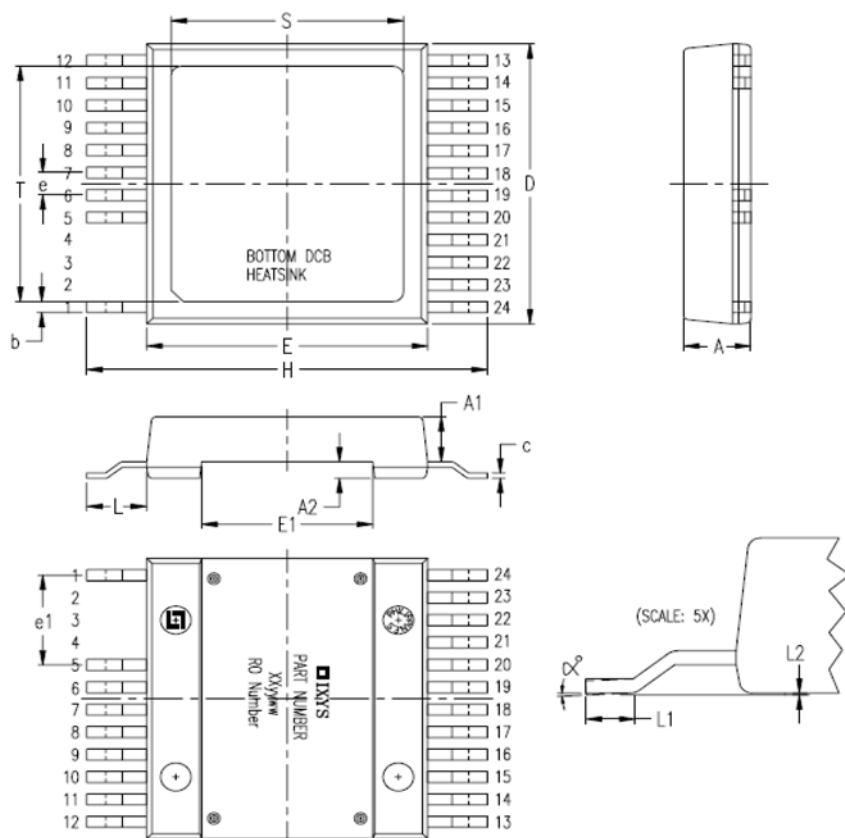
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Package Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
α	0	4°	0	4°

PIN: 1 = Gate
 5-12 = Emitter
 13-24 = Collector

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

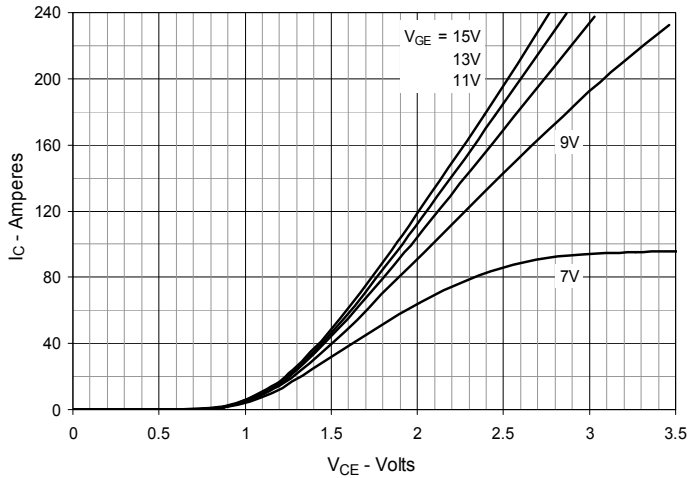


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

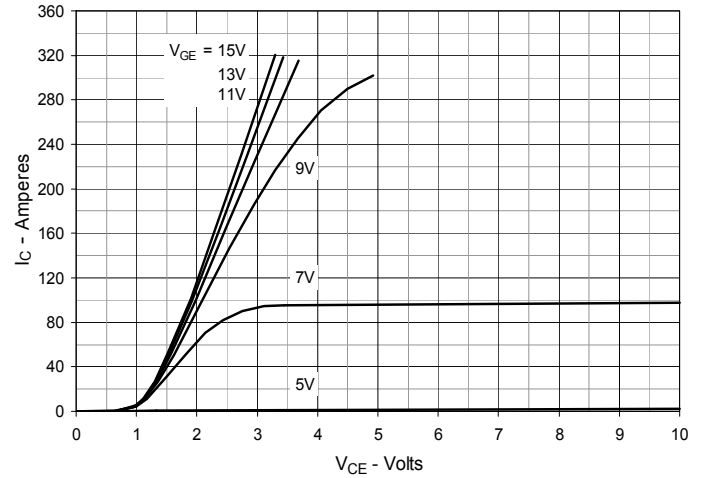


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

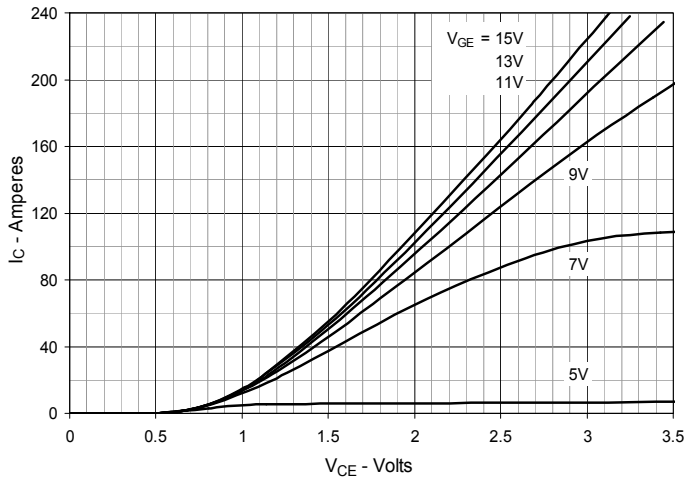


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

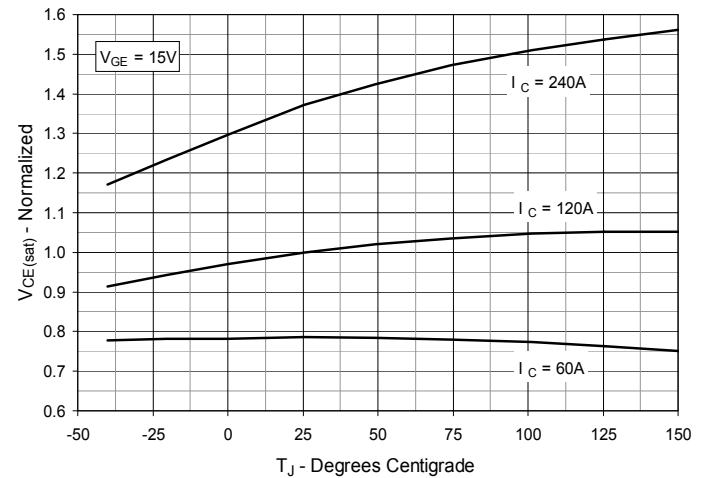


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

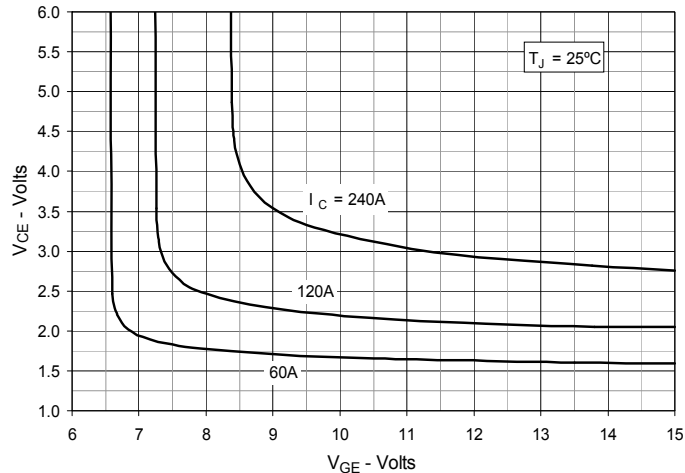


Fig. 6. Input Admittance

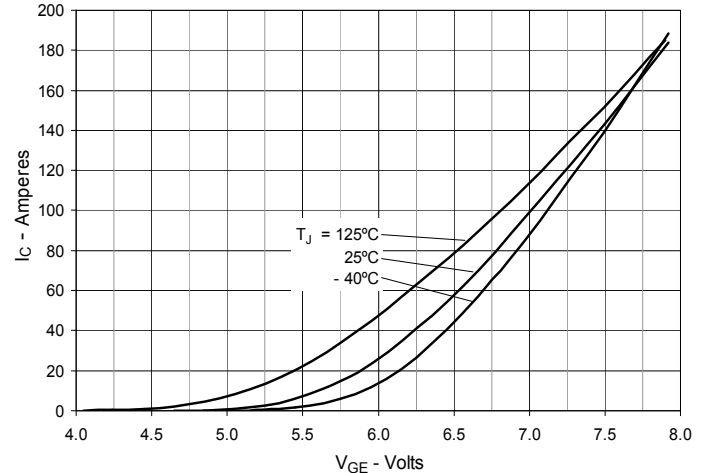


Fig. 7. Transconductance

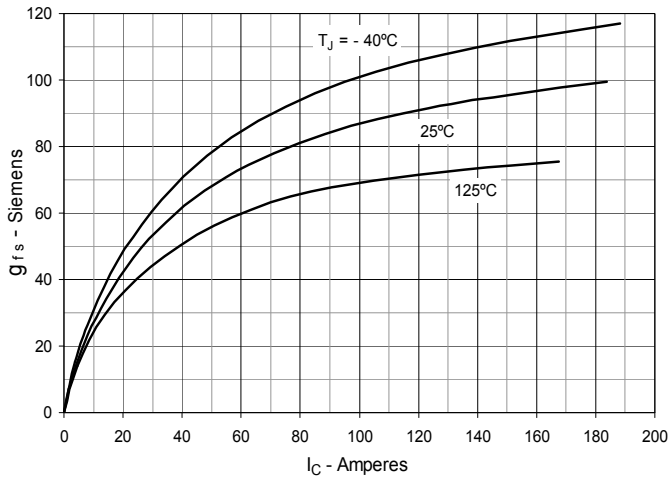


Fig. 8. Gate Charge

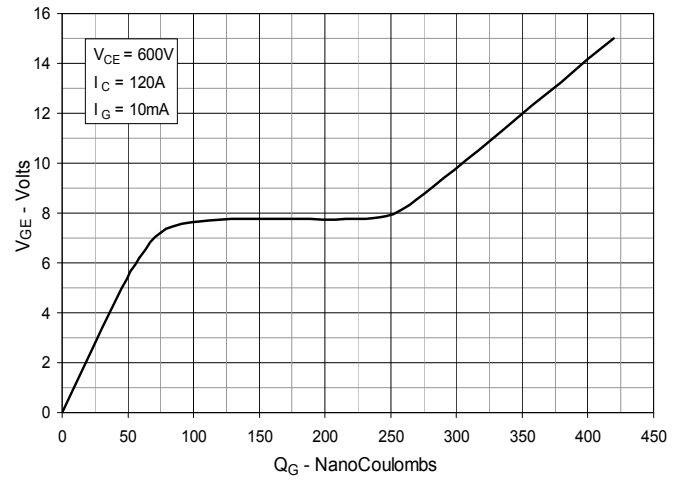


Fig. 9. Capacitance

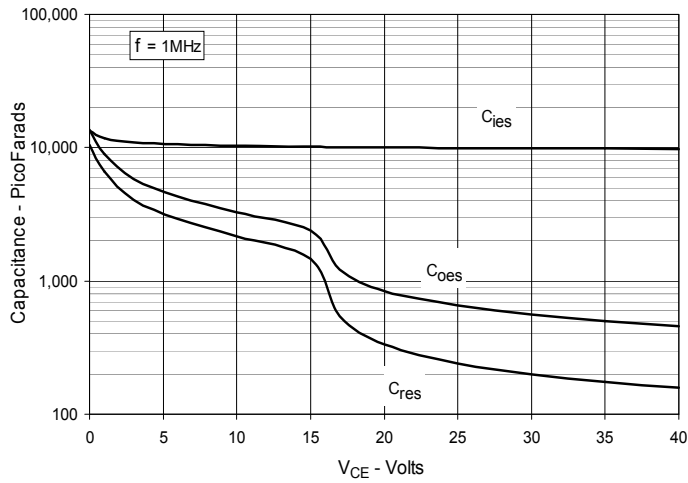


Fig. 10. Reverse-Bias Safe Operating Area

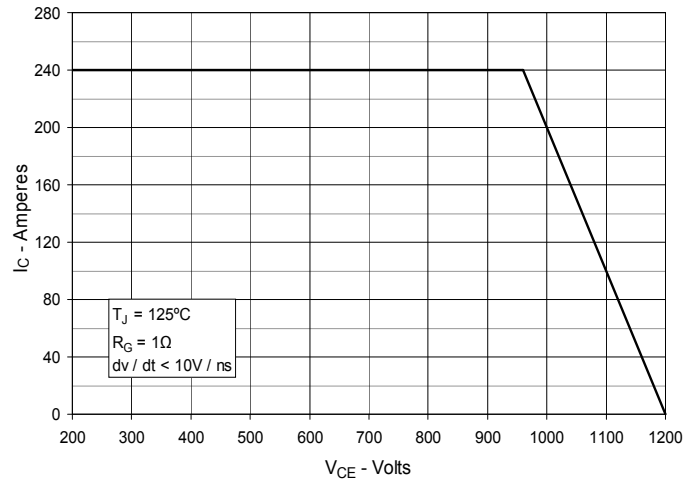


Fig. 11. Maximum Transient Thermal Impedance

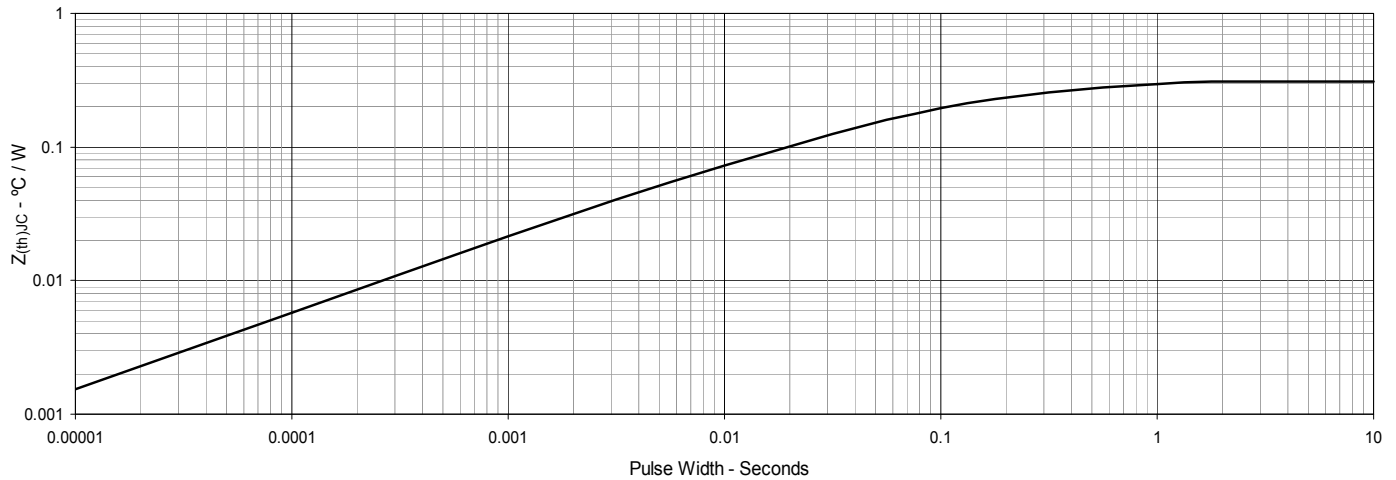


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

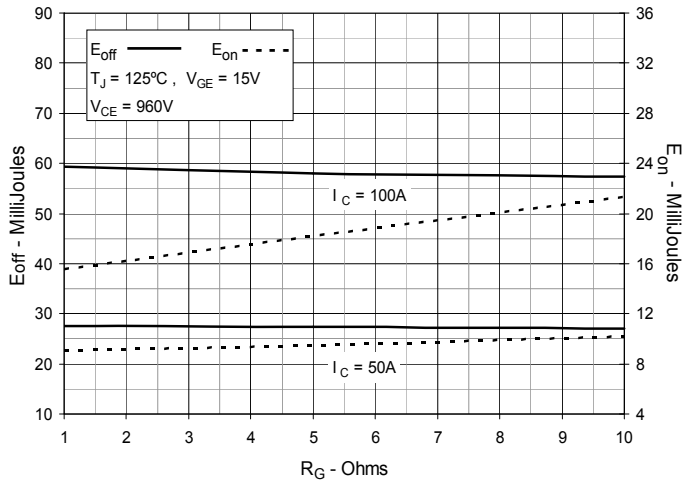


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

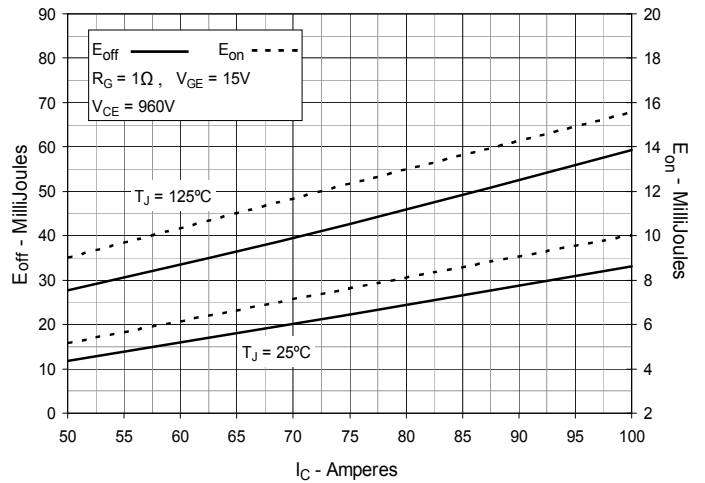


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

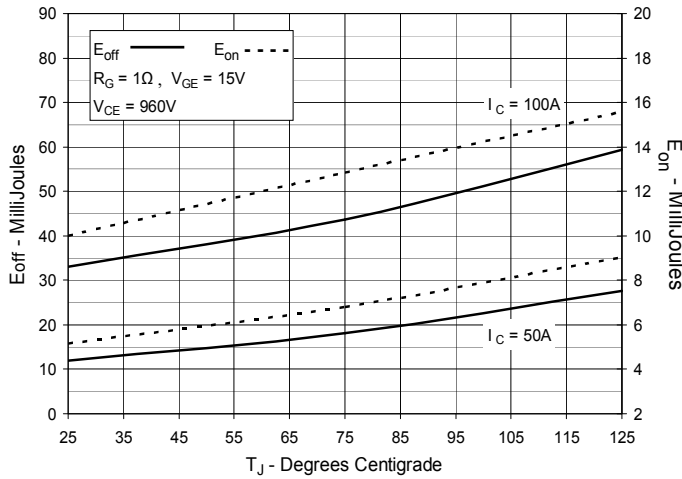


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

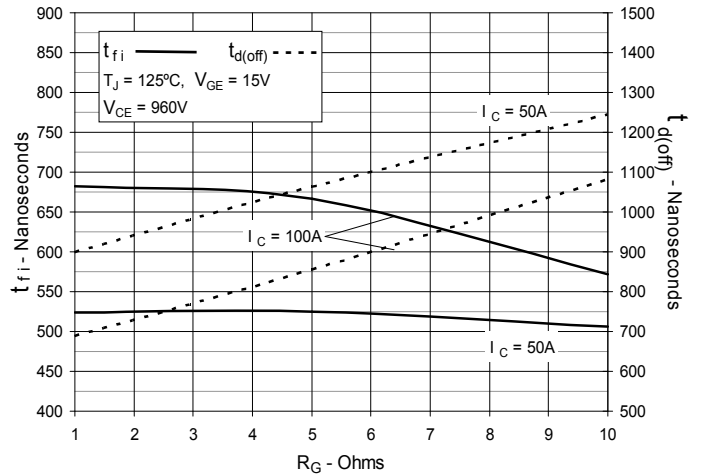


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

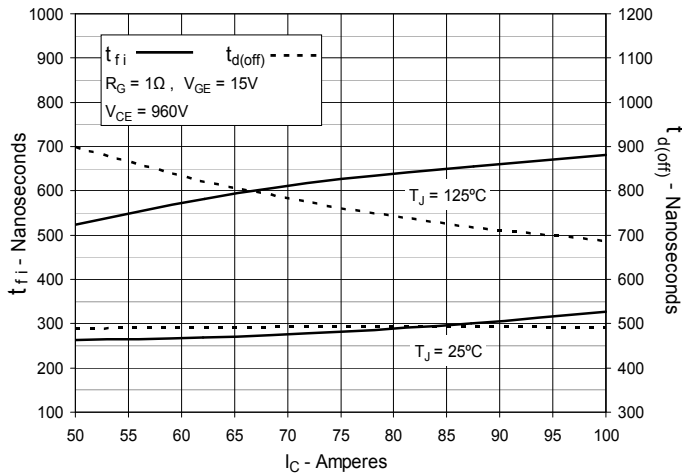


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

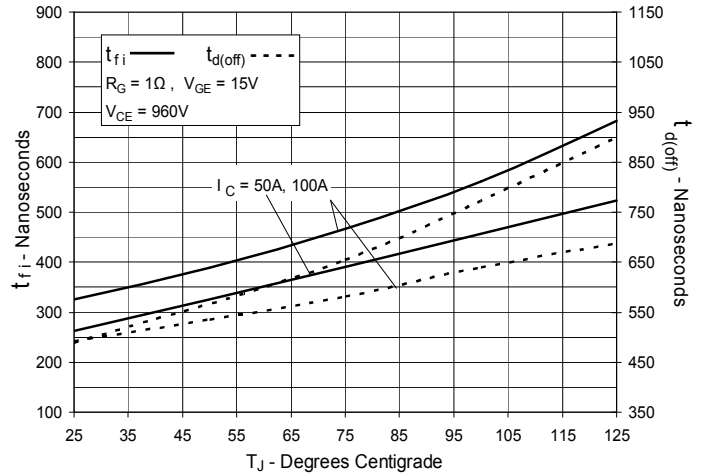


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

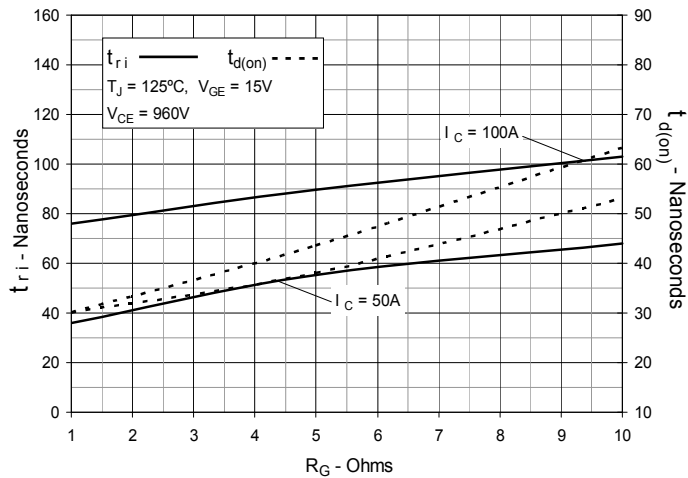


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

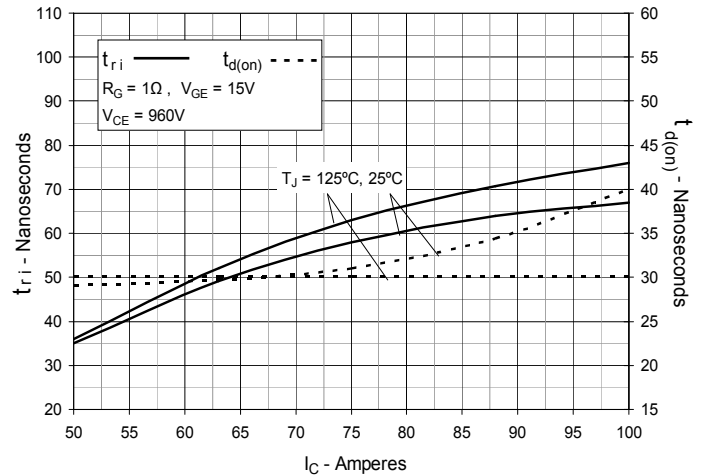


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

